

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend the paragraph starting at page 10, line 14, as follows:

To be more specific, the GaAs layer 31, $\text{Al}_{0.15}\text{Ga}_{0.85}\text{As}$ layer 32 and $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ layer 33 constituting the buffer layer 30 are formed at relatively fast growth rates, and the $\text{Al}_{0.4}\text{Ga}_{0.6}\text{As}$ layer 41 that is the ~~first~~ first layer of the multilayer structure 4 is formed at a slower growth rate than the growth rate of the buffer layer ~~3~~ 30.